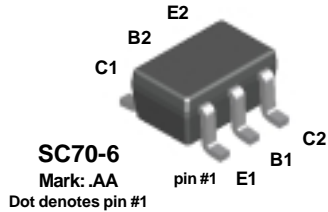
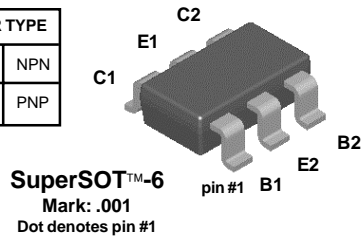


FFB2227A



TRANSISTOR TYPE			
C1	B1	E1	NPN
C2	B2	E2	PNP

FMB2227A



NPN & PNP General Purpose Amplifier

This complementary device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19 and 63. See FFB2222A (NPN) and FFB2907A (PNP) for characteristics.

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristic	Max		Units
		FFB2227A	FMB2227A	
P_D	Total Device Dissipation	300	700	mW
	Derate above 25°C	2.4	5.6	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180	$^\circ\text{C}/\text{W}$

NPN & PNP General Purpose Amplifier

(continued)

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}, I_B = 0$	30			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\ \mu\text{A}, I_E = 0$	60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\ \mu\text{A}, I_C = 0$	5.0			V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 50\text{ V}, I_E = 0$			30	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0\text{ V}, I_C = 0$			30	nA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}^*$ $I_C = 300\text{ mA}, V_{CE} = 10\text{ V}^*$	50 75 100 30			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 300\text{ mA}, I_B = 30\text{ mA}$			0.4 1.4	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$			1.3	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 50\text{ mA}, V_{CE} = 20\text{ V},$ $f = 100\text{ MHz}$		250		MHz
C_{obo}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 100\text{ kHz}$		4.0		pF
C_{ibo}	Input Capacitance	$V_{EB} = 2.0\text{ V}, I_C = 0, f = 100\text{ kHz}$		12		pF
NF	Noise Figure	$I_C = 100\ \mu\text{A}, V_{CE} = 10\text{ V},$ $R_S = 1.0\text{ k}\Omega, f = 1.0\text{ kHz}$		2.0		dB

SWITCHING CHARACTERISTICS

t_{on}	Turn-on Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA},$ $I_{B1} = 15\text{ mA}$		30		ns
t_d	Delay Time			8.0		ns
t_r	Rise Time			20		ns
t_{off}	Turn-off Time	$V_{CC} = 6.0\text{ V}, I_C = 150\text{ mA}$ $I_{B1} = I_{B2} = 15\text{ mA}$		80		ns
t_s	Storage Time			60		ns
t_f	Fall Time			20		ns

*Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

FFB2227A / FMB2227A

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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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